

DESCRIPTION

Typical applications are DC–DC converters, power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

FEATURES

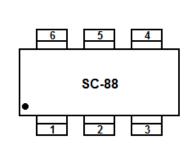
- Low Threshold Voltage (V_{GS(th)}: 0.5V...1.5V) makes it ideal for low voltage applications
- ESD Protected:1500V
- Available in SC-88 package

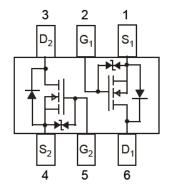
The BSS139D is available in SC-88 package

ORDERING INFORMATION

| Package Type | Part Number | | | | |
|--|--------------------|--|--|--|--|
| SC-88 | BSS139D | | | | |
| Note | SPQ: 3,000pcs/Reel | | | | |
| AiT provides all RoHS Compliant Products | | | | | |

PIN DESCRIPTION





ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted

| V _{DSS} , Drain-to-Source Voltage | 50Vdc |
|--|--------------|
| V _{GS} , Gate-to-Source Voltage - Continuous | ±20Vdc |
| Drain Current | |
| I _D , -Continuous @ T _A = 25°C | 200mA |
| I _{DM} , -Pulsed Drain Current (tp ≤10µs) | 800mA |
| P _D , Total Power Dissipation @ T _A = 25°C | 380mW |
| T _J , T _{STG} , Operating and Storage Temperature Range | -55°C ~150°C |
| R _{0JA} , Thermal Resistance – Junction–to–Ambient | 328°C/W |
| T _L , Maximum Lead Temperature for Soldering Purposes, for 10 seconds | 260°C |

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless otherwise noted

| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit | | |
|--------------------------------------|---------------------|--|------|------|------|-------|--|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | V _{GS} =0Vdc, I _D =250µAdc | 50 | - | - | Vdc | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =25Vdc, V _{GS} =0Vdc | - | - | 0.1 | μAdc | | |
| | | V _{DS} =50Vdc, V _{GS} =0Vdc | - | - | 0.5 | | | |
| Gate-Source Leakage Current | Igss | V _{GS} =±20Vdc, V _{DS} =0Vdc | - | - | ±10 | μAdc | | |
| ON CHARACTERISTICS NOTE1 | | | | | | | | |
| Gate–Source Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =1.0mAdc | 0.5 | - | 1.5 | Vdc | | |
| Static Drain-to-Source On-Resistance | R _{DS(on)} | V_{GS} =2.75Vdc, I_D <200mAdc, | | | | | | |
| | | T _A =-40°C to +85°C | - | 5.6 | 10 | Ohms | | |
| | | V _{GS} =5.0Vdc, I _D =200mAdc | - | - | 3.5 | | | |
| E I E I . d | G fs | V _{DS} =25Vdc, I _D =200mAdc, | 400 | | - | mmhos | | |
| Forward Transconductance | | f=1.0kHz | 100 | - | | | | |
| DYNAMIC CHARACTERISTICS | | | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =25Vdc, V _{GS} =0, f=1MHz | - | 22.8 | - | | | |
| Output Capacitance | Coss | V _{DS} =25Vdc, V _{GS} =0, f=1MHz | - | 3.5 | - | pF | | |
| Transfer Capacitance | Crss | V _{DS} =25Vdc, V _{GS} =0, f=1MHz | - | 2.9 | - | | | |
| SWITCHING CHARACTERISTICS NOTE2 | | | | | | | | |
| Turn-On Delay Time | t _{d(on)} | \\ -20\\d- -0.54- | - | 3.8 | - | ns | | |
| Turn-Off Delay Time | t _{d(off)} | $V_{DD} = 30 \text{Vdc}$, $I_D = 0.5 \text{Adc}$ | - | 19 | - | ns | | |

NOTE1: Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

NOTE2: Switching characteristics are independent of operating junction temperature.

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TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

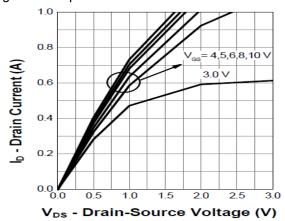


Figure 3. Transfer Characteristics

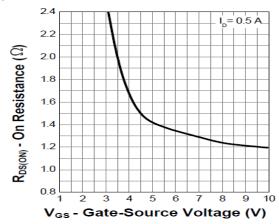


Figure 5. Drain-Source On Resistance

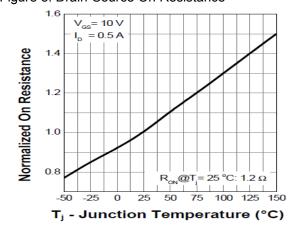


Figure 2. Drain-Source On Resistance

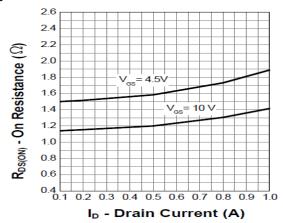


Figure 4. Gate Threshold Voltage

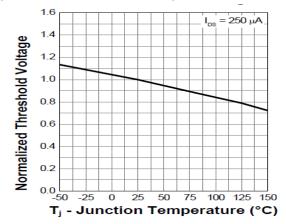
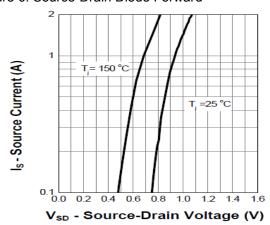
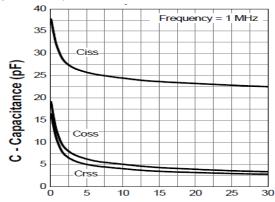


Figure 6. Source-Drain Diode Forward



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V_{DS} - Drain-Source Voltage (V)

Figure 9. Drain-Source On Resistance

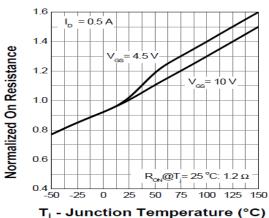


Figure 11. Drain-Source On Resistance

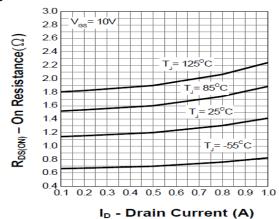


Figure 8. Gate Charge

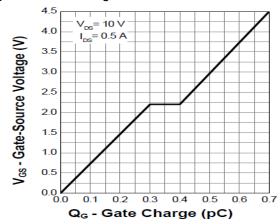


Figure 10. Drain-Source On Resistance

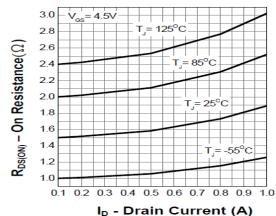
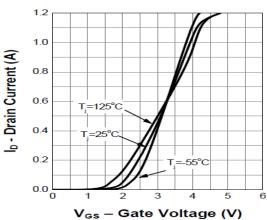


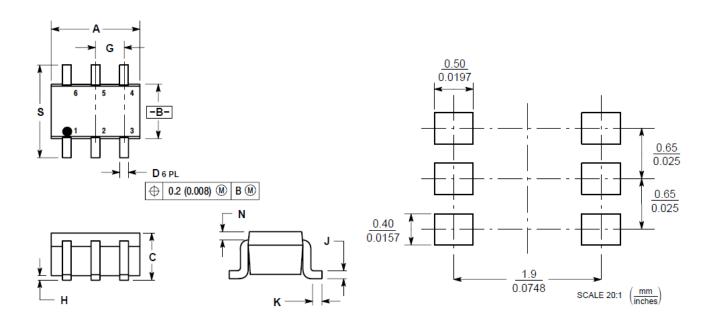
Figure 12. Transfer Characteristics



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PACKAGE INFORMATION

Dimension in SC-88 Package (Unit: mm)



| DIM | MILLIM | ETERS | INCHES | | |
|-----|----------|-------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 1.80 | 2.20 | 0.071 | 0.087 | |
| В | 1.15 | 1.35 | 0.045 | 0.053 | |
| С | 0.80 | 1.10 | 0.031 | 0.043 | |
| D | 0.10 | 0.30 | 0.004 | 0.012 | |
| G | 0.65 BSC | | 0.026 BSC | | |
| Н | - | 0.10 | - | 0.004 | |
| J | 0.10 | 0.25 | 0.004 | 0.010 | |
| K | 0.10 | 0.30 | 0.004 | 0.012 | |
| N | 0.20 REF | | 0.008 REF | | |
| S | 2.00 | 2.20 | 0.079 | 0.087 | |

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